

(3 Hours)

[Total Marks : 80

Instructions to candidates

Marks

- 1) Q.No. 1 is compulsory.
- 2) Solve any 3 questions from the remaining 5 questions.
- 3) Figures on right side indicate full marks.

~~Duration~~ Time - 3 hours

Max. Marks - 80

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|--------|---|----|
| Q.No 1 | a) Explain the various Connecting devices used in computer networks. | 05 |
| | b) Explain bit stuffing and unstuffing with respect to HDLC. | 05 |
| | c) Explain CSMA/CA method of random access. | 05 |
| | d) Compare TCP and UDP. | 05 |
| Q.No 2 | a) Explain the ISO-OSI model of networks with the help of neat diagrams. | 10 |
| | b) Explain the sliding window ARQ used for error control. | 10 |
| Q.No 3 | a) Explain the various station types, Configurations, response modes and Frame formats in HDLC. | 10 |
| | b) Draw the TCP header format with the help of a neat diagram. | 10 |
| Q.No.4 | a) Explain circuit switching, packet switching and message switching. | 10 |
| | b) Explain how routers use link state routing algorithm to create the routing table. | 10 |
| Q.No.5 | a) List the various options used in the IP datagram and explain each in brief. | 10 |
| | b) Draw and discuss the Ethernet frame format. | 10 |
| Q.No.6 | Write short notes on | |
| | a) Guided and unguided media. | 05 |
| | b) Open loop congestion control. | 05 |
| | c) PPP Header format | 05 |
| | d) Network topologies. | 05 |

MD-Con. 10763-15.

30/11/15

QP Code : 5901

ETRX

ICT

Max. Marks: 80

Time: 3 Hours.

N.B.

- 1) Question No. 1 is compulsory
- 2) Solve any three questions from remaining questions
- 3) Assume suitable data if necessary

1. Solve any four of the following (20)
 - (a) Explain predeposition and drive in steps in diffusion process.
 - (b) Classify and discuss in brief the types of Thin Film Deposition methods.
 - (c) What is Hall effect? Enlist important electrical parameters for which measurement is required before device processing begins.
 - (d) Explain the need of isolation in VLSI and list the methods to accomplish it?
 - (e) Explain SOI fabrication using bonded SOI and smart cut method.
2.
 - (a) Explain Czochralski method for Silicon crystal growth. What are its advantages? (10)
 - (b) What do you mean by Class of a clean room? Give the steps in a standard RCA cycle during wafer cleaning (10)
3.
 - (a) Explain Solid source diffusion system with neat diagram. Also give one example of each source for P-type and N-type diffusion. (10)
 - (b) Explain High K and Low K dielectrics with application of each. (05)
 - (c) What are the basic reactions in formation of SiO_2 in dry oxidation and wet oxidation? Explain where these methods are used during MOSFET fabrication process. (05)
4.
 - (a) Explain the fabrication process steps along with vertical cross-sectional views for CMOS inverter using N-well process (10)
 - (b) What are the different types of design rules? Draw layout of 2 input NAND gate as per lambda (λ) based design rules (Show units in lambda). (10)
5.
 - (a) Enlist important electrical parameters for which measurement is required before device processing begins. Also describe the experimental setup for the Four Probe method for resistivity measurement with the help of a neat diagram (10)
 - (b) Explain the difference between SOI Finfet and bulk Finfet? (03)
 - (c) State advantages of Finfet devices over single gate MOSFET devices. Also draw cross-sectional views of different multigate structures. (07)
6. Write short notes on any three of the following (20)
 - (a) MESFET Fabrication
 - (b) Carbon Nanotube Transistor
 - (c) SOI Technology
 - (d) Parametric tests and Functionality tests for IC testing

Course: B.E. (Sem VII) (REV. -2012) (CBSGS) (Electronics Engg.) (Prog T3227)

QP Code: 5901

Correction:

Q.no. 6

Read As:

Write short notes on the following. **(All)**

Instead of:

Write short notes on **any three** of the following.

Query Update time: 30/11/2015 12:45 PM

(3 Hours)

[Total Marks : 80

- 1) Question no. 1 is compulsory
- 2) Solve any three from the remaining five questions.
- 3) Assume suitable additional data if necessary.

Q1 Answer the following questions. (20)

- a) With the help of an example explain periodic task. List and explain the various types of tasks in an embedded system.
- b) With respect to power, performance and cost state and explain the associated design metrics for an embedded system.
- c) What are interrupts and explain the factors that contribute to interrupt response time in a system.
- d) Explain the structure of typical C source program for ARM based target processor. Typically list the various data types along-with memory size supported by a C compiler.

Q2 a) What is a task and various states that a task can lie in for an embedded environment. (10)

b) Explain briefly the problem of priority inversion and mechanism to prevent the same. (10)

Q3) a) State and explain the criteria for tasks schedulability and explain various scheduling mechanisms. (10)

b) Explain briefly the register structure of Cortex-M3 architecture along-with the function of various special registers. (10)

Q4) a) Distinguish between Cortex - M3 and M4 architecture and explain briefly the interrupt structure of M3 architecture. (08)

b) Explain the operation and significance of following MicroC/OS - II functions. (Any Three) (12)

a) OSInit(); b) OSSemPend(); & OSSemPost(); c) OSTaskCreate();

d) OSMboxPost(); & OSMboxPend();

Q5) a) Write a brief note to bring out the comparison between Cortex - M3, A8 and R4 architectures. (10)

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b) Explain the various inter- process/task communication tools like pipe, mailbox, message queue and semaphore used by an RTOS environment. (10)

Q6) Write short notes on (Any two) (20)

- a) Serial communication standard RS-232 and comparison with RS - 485.
- b) Low power features in Cortex - M 3 architecture.
- c) Black box and White box testing.

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SARDAR PATEL INSTITUTE OF TECHNOLOGY, ANCHERI (W) 11/2005
S. R. A. V.

Power Electronics-II

QP Code : 5939

(3 Hours)

[Total Marks :80

- N.B. : (1) Question no. 1 is compulsory.
 (2) Solve any three questions out of remaining five questions.
 (3) Figures to the right indicate full marks.
 (4) Solve one complete question together.
 (5) Assume suitable data wherever necessary.

1. Attempt any four from the following:-

- (a) What are the advantages of SVM over the conventional Sine wave PWM? Explain. 5
 (b) List the merits and demerits of online and offline UPS. 5
 (c) Explain regenerative braking for DC motors. 5
 (d) Explain in brief the effect of source inductance in single phase fully controlled bridge rectifier. 5
 (e) Explain the concept of UPS and give classification of UPS system. 5
2. (a) Explain clearly the steps involved in Space Vector Modulation for three phase voltage source inverter. 10
 (b) A single phase full-wave mid-point converter with freewheeling diode as shown below in Fig. Q2(b) is supplied from a 120V, 50 Hz supply with a source inductance of 0.33 mHenry. Assuming that the load current is continuous at 4A, find the overlap angle for
 (i) Transfer of current from a conducting thyristor to the commutating diode.
 (ii) From the commutating diode to a thyristor when the firing angle is 15 degree.

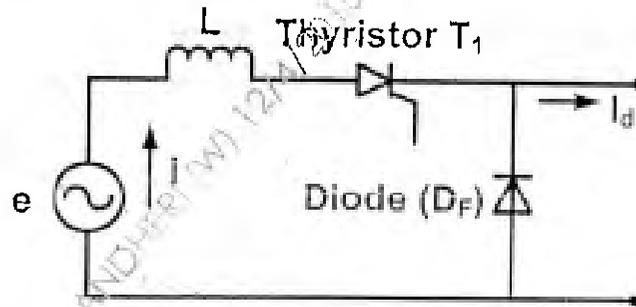


Fig.Q2. (b)

3. (a) Derive and explain the state-space model of Buck converter. 10
 (b) Explain the PI (Proportional + Integral) control of DC-DC converter with the help of neat diagram. 10
4. (a) Derive the expressions for output voltage and current for a single phase fully controlled bridge rectifier with source inductance using equivalent circuit. 8
 (b) What are SMPS? Give classification and explain any SMPS circuit in detail. 6
 (c) Draw and explain the battery charging circuit involving power electronics system. 6

[TURN OVER

5. (a) A separately excited DC motor is supplied from 230V, 50Hz source through a single-phase half wave controlled converter. Its field is fed through single-phase semi-converter with zero degree firing angle delay. Motor resistance = 0.70Ω , Motor constant = 0.5 volts sec/rad. For a rated load torque of 15 NM at 1000 rpm and for continuous ripple-free current, determine:

- (i) Firing angle delay of the armature converter.
- (ii) RMS value of thyristor & freewheeling diode current.
- (iii) Input power factor of the armature current.

(b) Explain various methods of speed control for 3-phase induction motor. 10

6. Write short notes on:

- (a) Comparison of fly-back and forward converters used in SMPS. 7
- (b) Power electronics applications in induction heating. 6
- (c) Slip power recovery scheme for induction motor using Kramer Drive below sub-synchronous speed. 7